Abstract Submitted
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Quantum Hall Effect in Bernal-stacked tetralayer graphene YANMENG SHI, SHI CHE, TIMOTHY ESPIRITU, ZIQI PI, Department of Physics and Astronomy, University of California Riverside, Riverside, CA 91765, TAKASHI TANIGUCHI, KENJI WATANABE, National Insitute for Materials Science, 1-1 Namiki, Tsukuba, Japan, CHUN NING LAU, Department of Physics and Astronomy, University of California Riverside, Riverside, CA 91765 — Bernal-stacked few layer graphene is of particular interest due to its unique tunable band structure. Here we study the electric transport of Bernal-stack tetralayer graphene that are encapsulated by boron nitride sheets. The device shows a clear Landau fan with multiple Landau level crossing features. We will present the dependence of its quantum Hall properties on electric and magnetic fields, and compare with theoretical calculations.

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